



# BUK764R0-40E

N-channel TrenchMOS standard level FET

28 July 2016

Product data sheet

## 1. General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

## 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

## 4. Quick reference data

Table 1. Quick reference data

| Symbol                         | Parameter                        | Conditions                                                                                                               |     | Min | Typ  | Max | Unit |
|--------------------------------|----------------------------------|--------------------------------------------------------------------------------------------------------------------------|-----|-----|------|-----|------|
| V <sub>DS</sub>                | drain-source voltage             | T <sub>J</sub> ≥ 25 °C; T <sub>J</sub> ≤ 175 °C                                                                          |     | -   | -    | 40  | V    |
| I <sub>D</sub>                 | drain current                    | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>                                                  | [1] | -   | -    | 75  | A    |
| P <sub>tot</sub>               | total power dissipation          | T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>                                                                          |     | -   | -    | 182 | W    |
| <b>Static characteristics</b>  |                                  |                                                                                                                          |     |     |      |     |      |
| R <sub>DS(on)</sub>            | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 11</a>                           |     | -   | 3.3  | 4   | mΩ   |
| <b>Dynamic characteristics</b> |                                  |                                                                                                                          |     |     |      |     |      |
| Q <sub>GD</sub>                | gate-drain charge                | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> |     | -   | 15.5 | -   | nC   |

[1] Continuous current is limited by package.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                  | Graphic symbol                                                                                |
|-----|--------|-----------------------------------|-----------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|
| 1   | G      | gate                              | <br>D2PAK (SOT404) | <br>mbb076 |
| 2   | D      | drain                             |                                                                                                     |                                                                                               |
| 3   | S      | source                            |                                                                                                     |                                                                                               |
| mb  | D      | mounting base; connected to drain |                                                                                                     |                                                                                               |

## 6. Ordering information

Table 3. Ordering information

| Type number  | Package |                                                                                  |         |
|--------------|---------|----------------------------------------------------------------------------------|---------|
|              | Name    | Description                                                                      | Version |
| BUK764R0-40E | D2PAK   | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404  |

## 7. Marking

Table 4. Marking codes

| Type number  | Marking code |
|--------------|--------------|
| BUK764R0-40E | BUK764R0-40E |

## 8. Limiting values

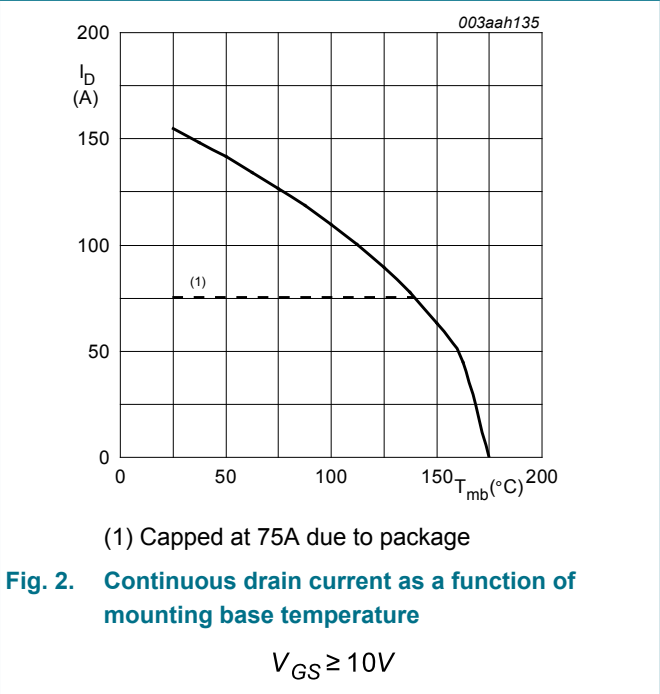
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter               | Conditions                                                                                  |                     | Min | Max | Unit |
|-----------|-------------------------|---------------------------------------------------------------------------------------------|---------------------|-----|-----|------|
| $V_{DS}$  | drain-source voltage    | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$                                          |                     | -   | 40  | V    |
| $V_{DGR}$ | drain-gate voltage      | $R_{GS} = 20\text{ k}\Omega$                                                                |                     | -   | 40  | V    |
| $V_{GS}$  | gate-source voltage     | $T_j \leq 175\text{ °C}$ ; DC                                                               |                     | -20 | 20  | V    |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                            |                     | -   | 182 | W    |
| $I_D$     | drain current           | $T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 2</a>                   | <a href="#">[1]</a> | -   | 75  | A    |
|           |                         | $T_{mb} = 100\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 2</a>                  | <a href="#">[1]</a> | -   | 75  | A    |
| $I_{DM}$  | peak drain current      | $T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <a href="#">Fig. 3</a> |                     | -   | 620 | A    |
| $T_{stg}$ | storage temperature     |                                                                                             |                     | -55 | 175 | °C   |
| $T_j$     | junction temperature    |                                                                                             |                     | -55 | 175 | °C   |

| Symbol               | Parameter                                    | Conditions                                                                                                                                                            |        | Min | Max | Unit |
|----------------------|----------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------|-----|-----|------|
| Source-drain diode   |                                              |                                                                                                                                                                       |        |     |     |      |
| I <sub>S</sub>       | source current                               | T <sub>mb</sub> = 25 °C                                                                                                                                               | [1]    | -   | 75  | A    |
| I <sub>SM</sub>      | peak source current                          | pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>mb</sub> = 25 °C                                                                                                               |        | -   | 620 | A    |
| Avalanche ruggedness |                                              |                                                                                                                                                                       |        |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 75 A; V <sub>sup</sub> ≤ 40 V; R <sub>GS</sub> = 50 Ω;<br>V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped;<br><a href="#">Fig. 4</a> | [2][3] | -   | 302 | mJ   |

- [1] Continuous current is limited by package.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.



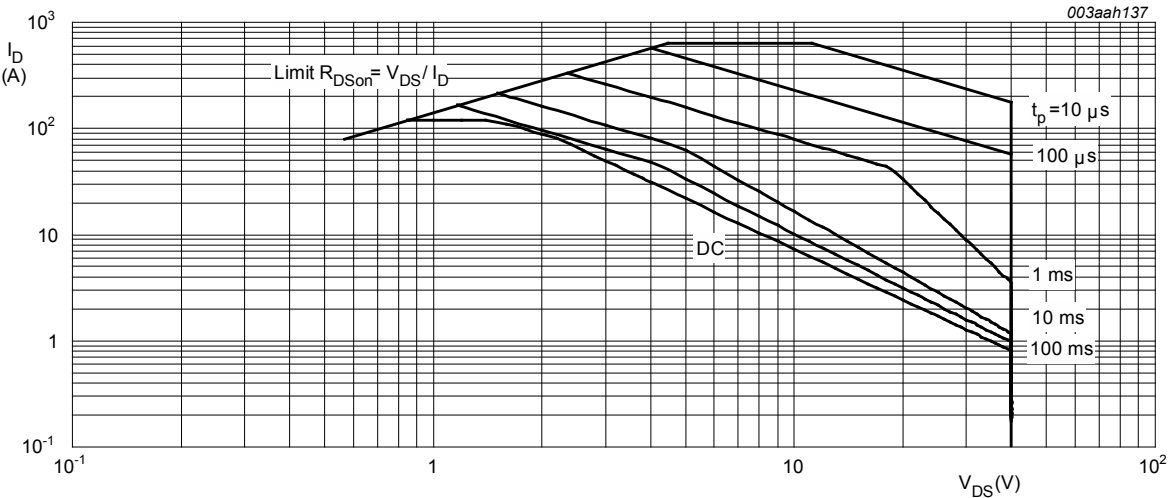


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}\text{C}$ ;  $I_{DM}$  is a single pulse

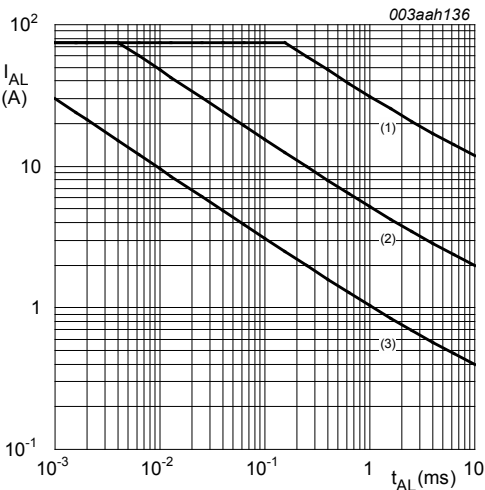


Fig. 4. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1)  $T_j(\text{init}) = 25^{\circ}\text{C}$ ; (2)  $T_j(\text{init}) = 150^{\circ}\text{C}$ ; (3) Repetitive Avalanche

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions                                            | Min | Typ | Max  | Unit |
|----------------|---------------------------------------------------|-------------------------------------------------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | <a href="#">Fig. 5</a>                                | -   | -   | 0.82 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | minimum footprint; mounted on a printed-circuit board | -   | 50  | -    | K/W  |

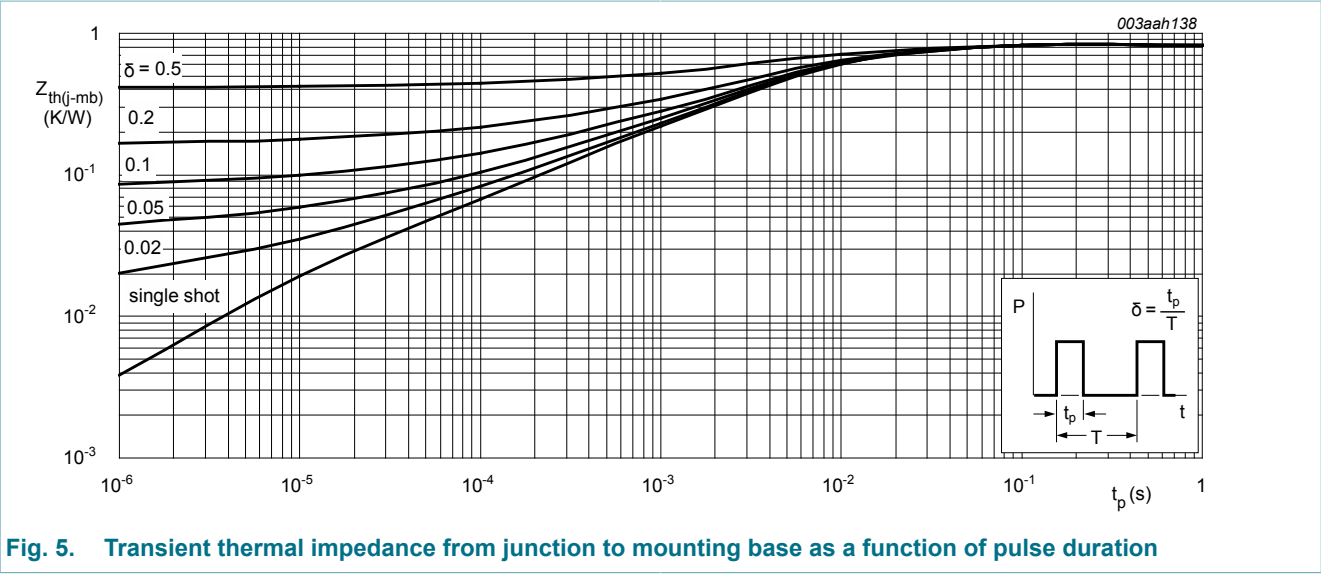


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

| Symbol                  | Parameter                        | Conditions                                                                                                                          |  | Min | Typ  | Max | Unit |
|-------------------------|----------------------------------|-------------------------------------------------------------------------------------------------------------------------------------|--|-----|------|-----|------|
| Static characteristics  |                                  |                                                                                                                                     |  |     |      |     |      |
| V <sub>(BR)DSS</sub>    | drain-source breakdown voltage   | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                              |  | 40  | -    | -   | V    |
|                         |                                  | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = -55 °C                                                             |  | 36  | -    | -   | V    |
| V <sub>GS(th)</sub>     | gate-source threshold voltage    | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = 25 °C; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a> |  | 2.4 | 3    | 4   | V    |
|                         |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = -55 °C; <a href="#">Fig. 10</a>                         |  | -   | -    | 4.5 | V    |
|                         |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = 175 °C; <a href="#">Fig. 10</a>                         |  | 1   | -    | -   | V    |
| I <sub>DSS</sub>        | drain leakage current            | V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                               |  | -   | 0.12 | 1   | μA   |
|                         |                                  | V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 175 °C                                                              |  | -   | -    | 500 | μA   |
| I <sub>GSS</sub>        | gate leakage current             | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                               |  | -   | 2    | 100 | nA   |
|                         |                                  | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                              |  | -   | 2    | 100 | nA   |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 11</a>                                      |  | -   | 3.3  | 4   | mΩ   |
|                         |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 175 °C; <a href="#">Fig. 12</a> ; <a href="#">Fig. 11</a>           |  | -   | -    | 7.6 | mΩ   |
| Dynamic characteristics |                                  |                                                                                                                                     |  |     |      |     |      |
| Q <sub>G(tot)</sub>     | total gate charge                | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>            |  | -   | 54   | -   | nC   |
| Q <sub>GS</sub>         | gate-source charge               |                                                                                                                                     |  | -   | 13.6 | -   | nC   |
| Q <sub>GD</sub>         | gate-drain charge                |                                                                                                                                     |  | -   | 15.5 | -   | nC   |

| Symbol              | Parameter                    | Conditions                                                                                                   |  | Min | Typ  | Max  | Unit |
|---------------------|------------------------------|--------------------------------------------------------------------------------------------------------------|--|-----|------|------|------|
| C <sub>iss</sub>    | input capacitance            | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a> |  | -   | 3304 | 4405 | pF   |
| C <sub>oss</sub>    | output capacitance           |                                                                                                              |  | -   | 634  | 761  | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance |                                                                                                              |  | -   | 333  | 456  | pF   |
| t <sub>d(on)</sub>  | turn-on delay time           | V <sub>DS</sub> = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 10 V;<br>R <sub>G(ext)</sub> = 5 Ω         |  | -   | 22   | -    | ns   |
| t <sub>r</sub>      | rise time                    |                                                                                                              |  | -   | 20   | -    | ns   |
| t <sub>d(off)</sub> | turn-off delay time          |                                                                                                              |  | -   | 43   | -    | ns   |
| t <sub>f</sub>      | fall time                    |                                                                                                              |  | -   | 20   | -    | ns   |
| L <sub>D</sub>      | internal drain inductance    | from upper edge of drain mounting base to center of die                                                      |  | -   | 2.5  | -    | nH   |
| L <sub>S</sub>      | internal source inductance   | from source lead to source bonding pad                                                                       |  | -   | 7.5  | -    | nH   |
| Source-drain diode  |                              |                                                                                                              |  |     |      |      |      |
| V <sub>SD</sub>     | source-drain voltage         | I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 16</a>                |  | -   | 0.84 | 1.2  | V    |
| t <sub>rr</sub>     | reverse recovery time        | I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V;                               |  | -   | 31.1 | -    | ns   |
| Q <sub>r</sub>      | recovered charge             | V <sub>DS</sub> = 25 V                                                                                       |  | -   | 28.9 | -    | nC   |

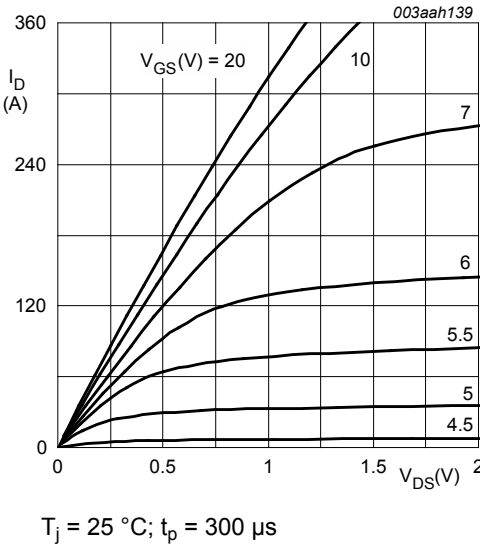


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

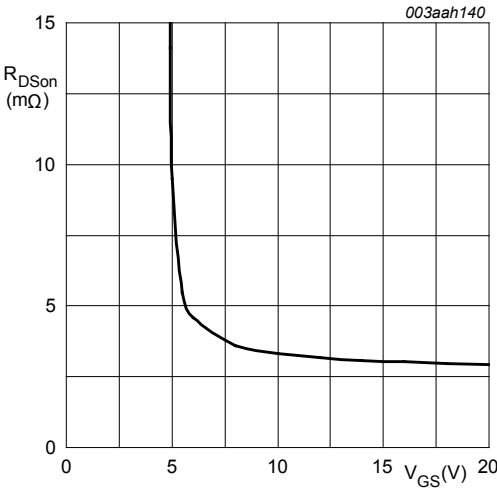


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ °C}; I_D = 25\text{ A}$

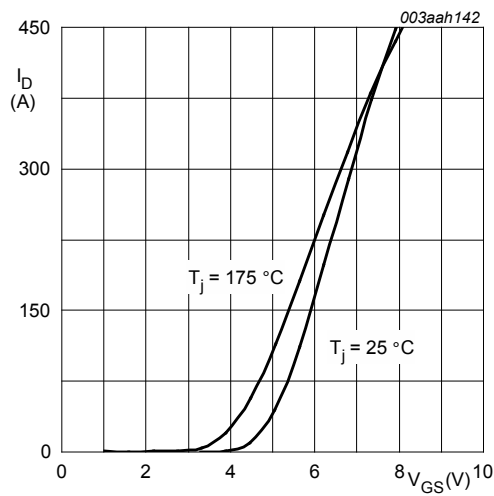


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

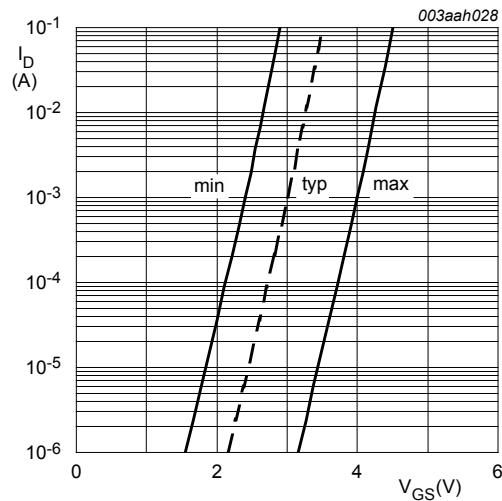


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$T_J = 25^{\circ}C; V_{DS} = 5V$

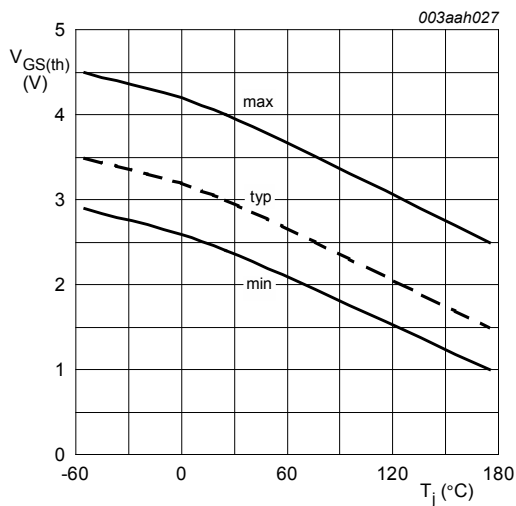


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

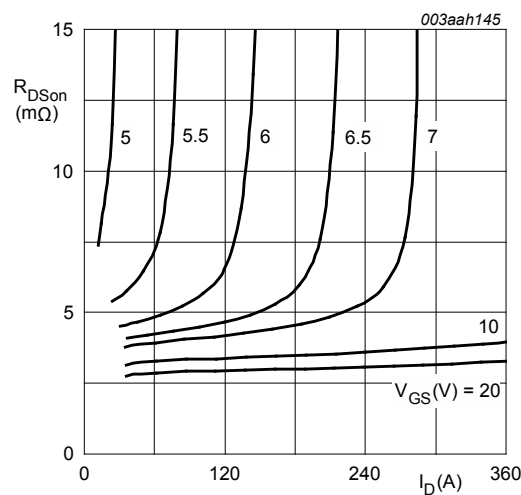
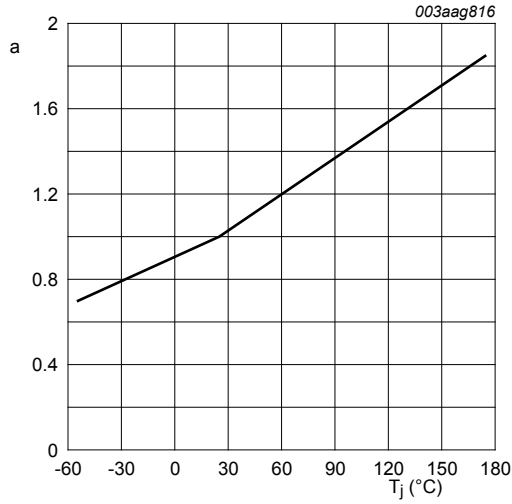


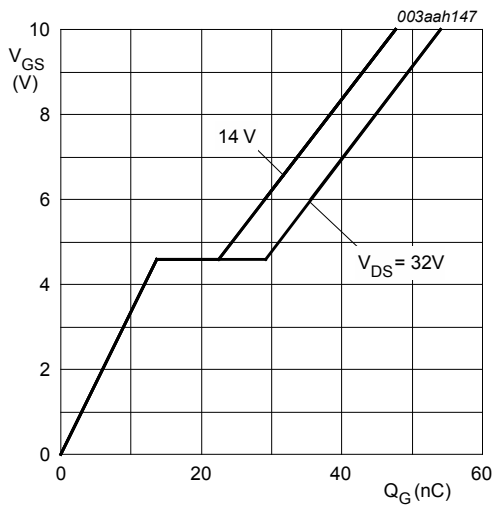
Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_J = 25^{\circ}C; t_p = 300 \mu s$



**Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

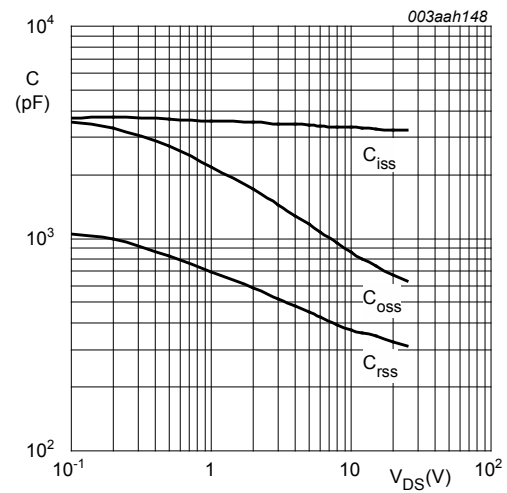


**Fig. 14. Gate-source voltage as a function of gate charge; typical values**

$$T_j = 25^\circ\text{C}; I_D = 25\text{A}$$



**Fig. 13. Gate charge waveform definitions**



**Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

$$V_{GS} = 0\text{V}; f = 1\text{MHz}$$

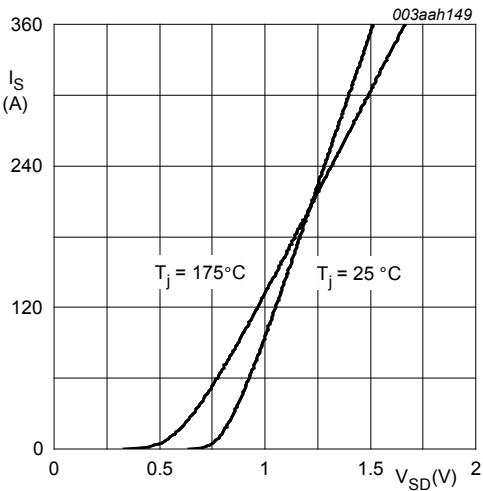


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values  
 $V_{GS} = 0\text{V}$

11. Package outline



Fig. 17. Package outline D2PAK (SOT404)

## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
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